NPN Silicon Epitaxial Planar Transistor

High current application

MAXIMUM RATINGS (Ta=25 unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	1.5	A
Total Power Dissipation	P_{tot}	0.5 1[1)]	W
Junction Temperature	T_j	150	
Storage Temperature	T_{stg}	-55~+150	

1) When mounted on a 250 mm² X 0.8 t ceramic substrate.

Characteristics at Ta = 25

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE} = 2 V, I_C = 500 mA Current Gain Group O	h_{FE}	100	-	200	-
Y	h_{FE}	160	-	320	-
Collector Base Breakdown Voltage at I_C = 1 mA	$V_{(BR)CBO}$	30	-	-	V
Collector Emitter Breakdown Voltage at I_C = 10 mA	$V_{(BR)C\ I\ d}$		⌉	V	-

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